

DOCKET NO. PHNL000195

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Liang et al.

Examiner: Lewis

Application No.: 09/829,797

Art Unit: 2822

Filed: April 10, 2001

For: SEMICONDUCTOR DEVICE WITH ISOLATED INTERMETAL DIELECTRICS

Box AF
Commissioner for Patents
Washington D.C. 20231

AMENDMENT

Sir:

In response to the final Office Action of September 26, 2002, Applicants respectfully request that the above-identified application be reconsidered in view of the amendments and remarks that follow, and that the application be passed to issue.

FAX RECEIVED

In the Claims

NOV 07 2002

Please amend the claims as follows:

TECHNOLOGY CENTER 2800

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1. (AMENDED) A semiconductor device comprising a bond pad structure, which bond pad structure comprises a bond pad disposed above at least one layered structure, wherein the layered structure comprises a metal layer and a layer of dielectric material, characterized in that via lines are present in the layer of a dielectric material, which via lines are connected to the metal layer to form isolated areas filled with dielectric material.

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